

N-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The μ PA1871 is a switching device which can be driven directly by a 2.5-V power source.

The μ PA1871 features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

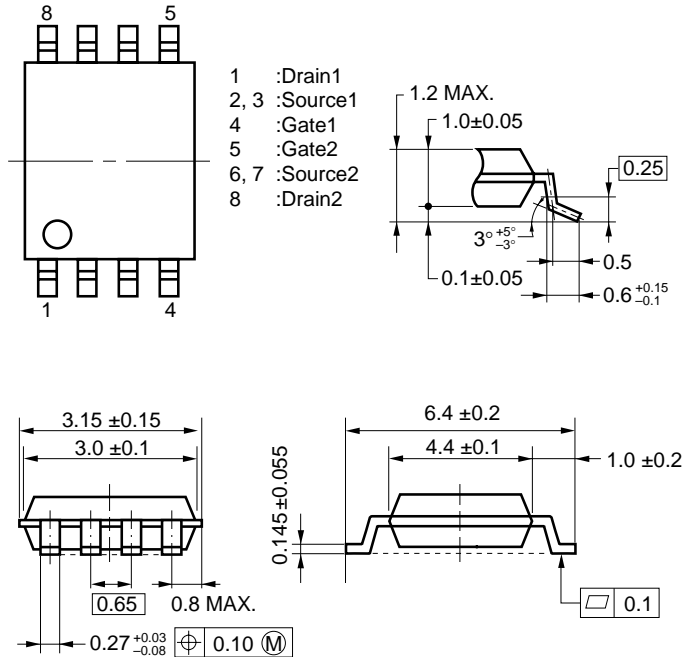
FEATURES

- Can be driven by a 2.5-V power source
- Low on-state resistance
 $R_{DS(on)1} = 26.0 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.5 \text{ V, } I_D = 3.0 \text{ A)}$
 $R_{DS(on)2} = 27.0 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.0 \text{ V, } I_D = 3.0 \text{ A)}$
 $R_{DS(on)3} = 38.0 \text{ m}\Omega \text{ MAX. (} V_{GS} = 2.5 \text{ V, } I_D = 3.0 \text{ A)}$
- Built-in G-S protection diode against ESD

ORDERING INFORMATION

PART NUMBER	PACKAGE
μ PA1871GR-9JG	Power TSSOP8

PACKAGE DRAWING (Unit: mm)

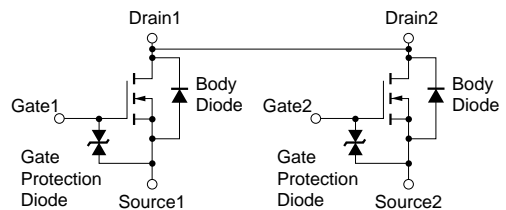


ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage	V _{DSS}	30	V
Gate to Source Voltage	V _{GSS}	±12	V
Drain Current (DC)	I _{D(DC)}	±6.0	A
Drain Current (pulse) ^{Note1}	I _{D(pulse)}	±80	A
Total Power Dissipation ^{Note2}	P _T	2.0	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

- Notes 1. PW ≤ 10 μs, Duty Cycle ≤ 1%
 2. Mounted on ceramic substrate of 50 cm² x 1.1 mm

EQUIVALENT CIRCUIT



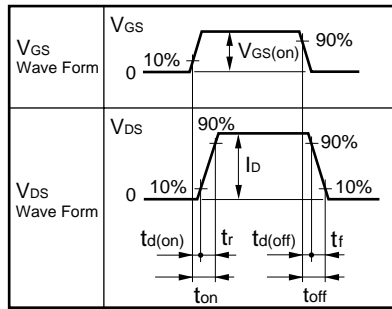
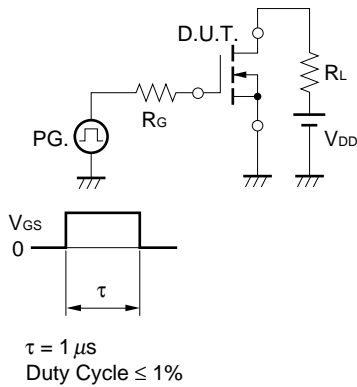
Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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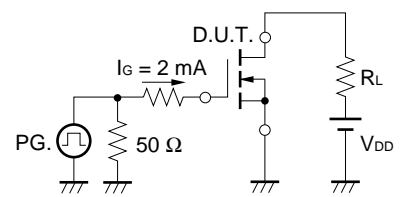
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±12 V, V _{DS} = 0 V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	0.5	1.0	1.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = 10 V, I _D = 3.0 A	5			S
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = 4.5 V, I _D = 3.0 A	15.0	20.5	26.0	mΩ
	R _{DS(on)2}	V _{GS} = 4.0 V, I _D = 3.0 A	16.0	21.5	27.0	mΩ
	R _{DS(on)3}	V _{GS} = 2.5 V, I _D = 3.0 A	21.0	27.8	38.0	mΩ
Input Capacitance	C _{iss}	V _{DS} = 10 V		930		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		220		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		105		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 10 V, I _D = 3.0 A		55		ns
Rise Time	t _r	V _{GS(on)} = 4.0 V		180		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		260		ns
Fall Time	t _f			230		ns
Total Gate Charge	Q _G	V _{DD} = 24 V		9		nC
Gate to Source Charge	Q _{GS}	V _{GS} = 4.0 V		2		nC
Gate to Drain Charge	Q _{GD}	I _D = 6.0 A		4		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 6.0 A, V _{GS} = 0 V		0.80		V
Reverse Recovery Time	t _{rr}	I _F = 6.0 A, V _{GS} = 0 V		180		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 50 A/μs		120		nC

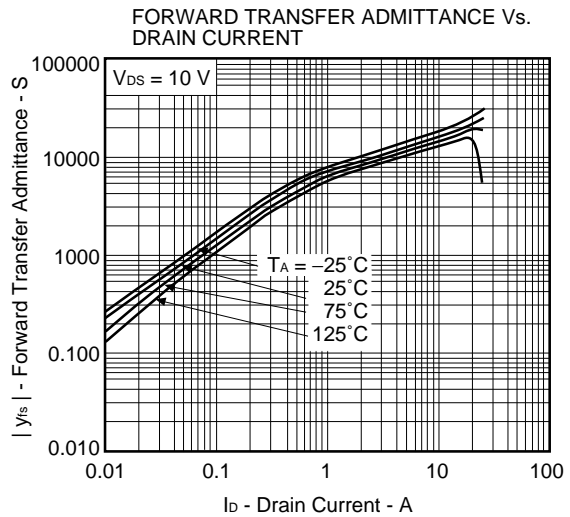
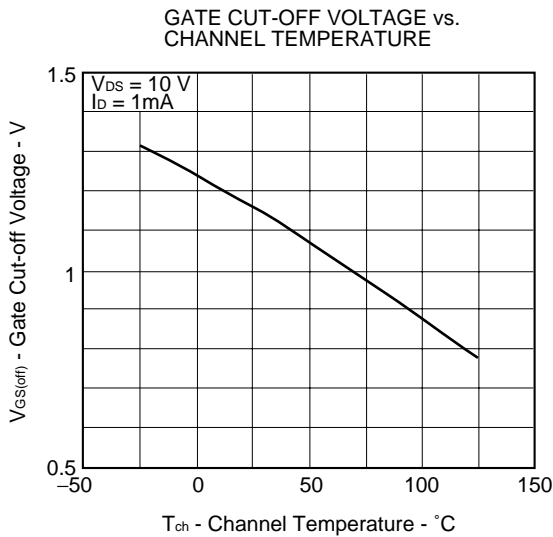
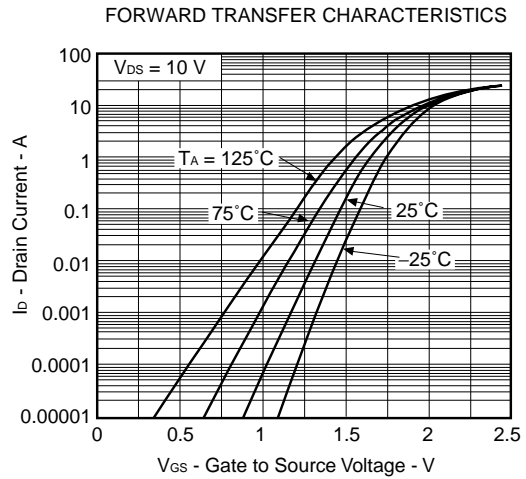
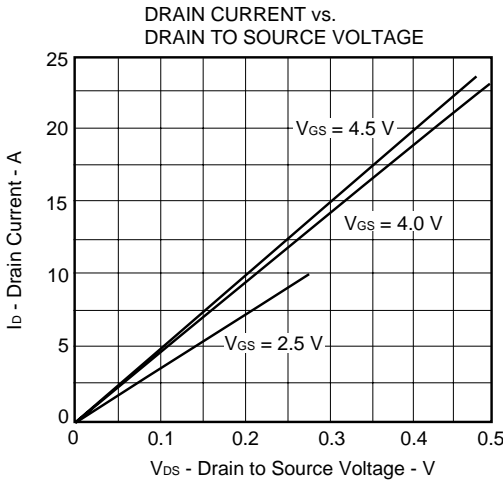
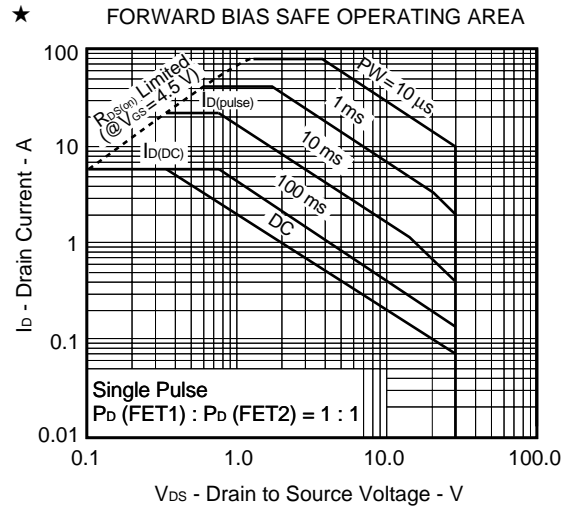
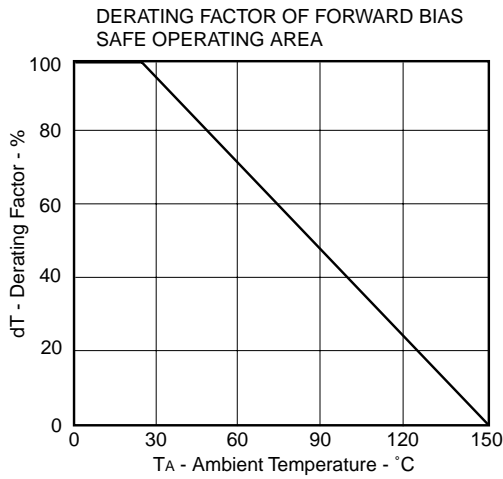
TEST CIRCUIT 1 SWITCHING TIME

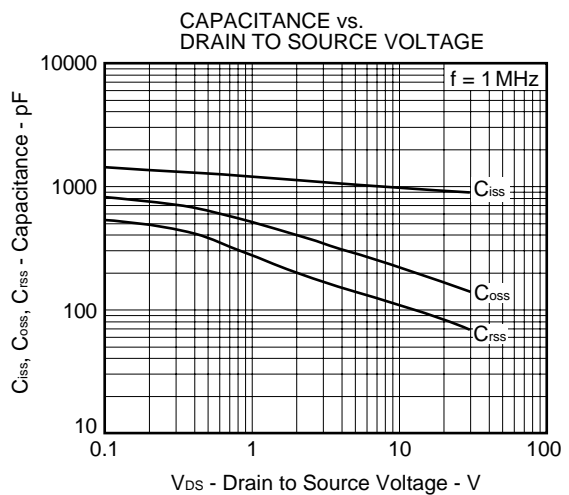
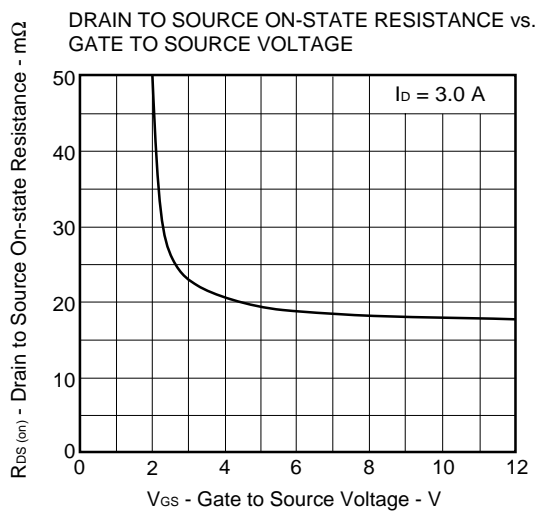
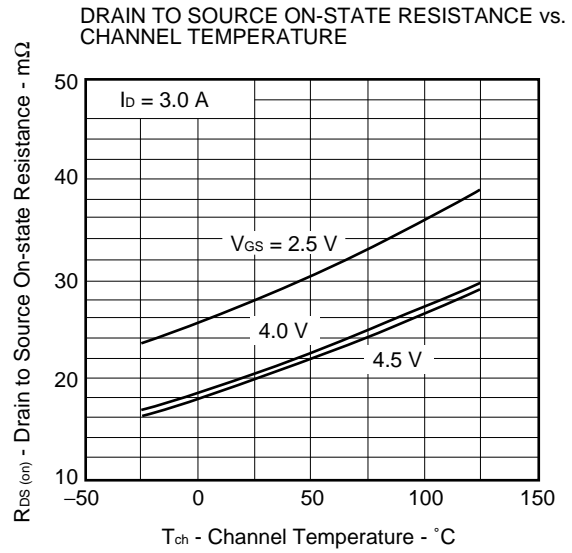
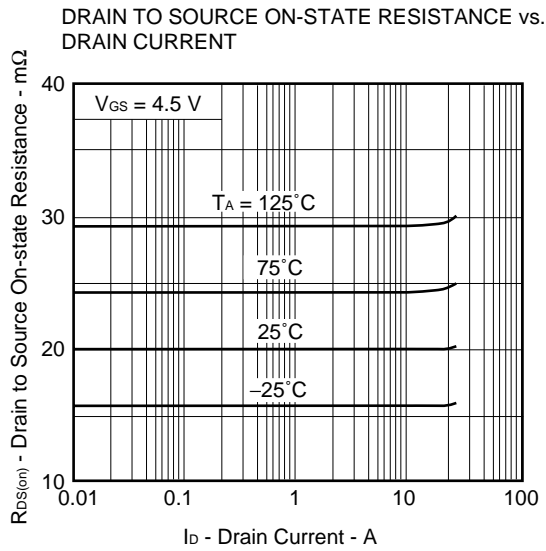
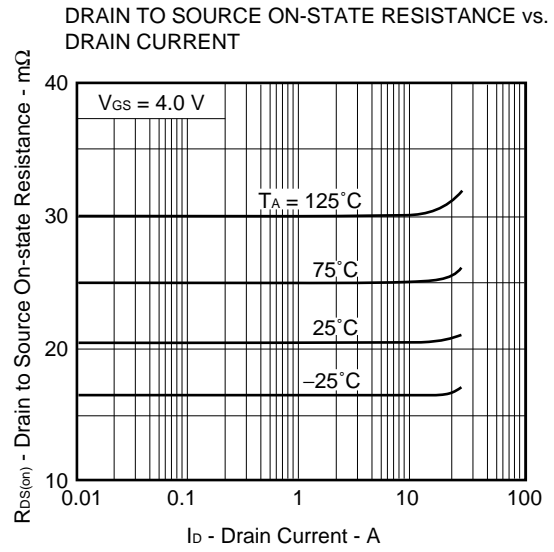
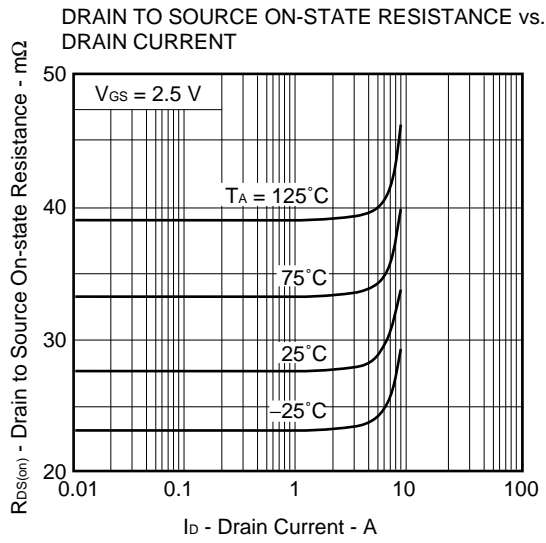


TEST CIRCUIT 2 GATE CHARGE

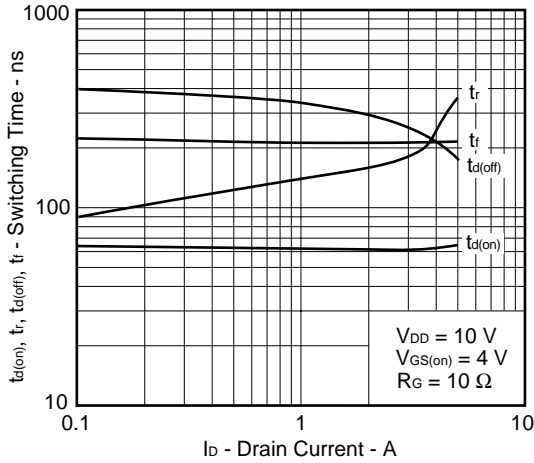


TYPICAL CHARACTERISTICS (T_A = 25°C)

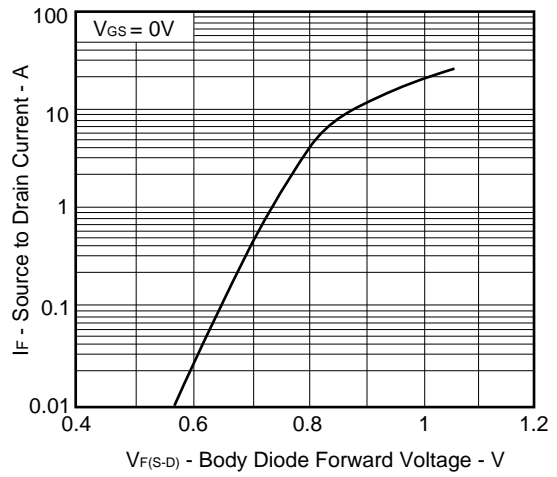




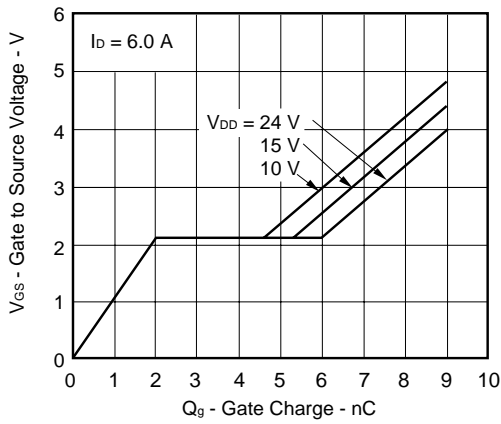
SWITCHING CHARACTERISTICS



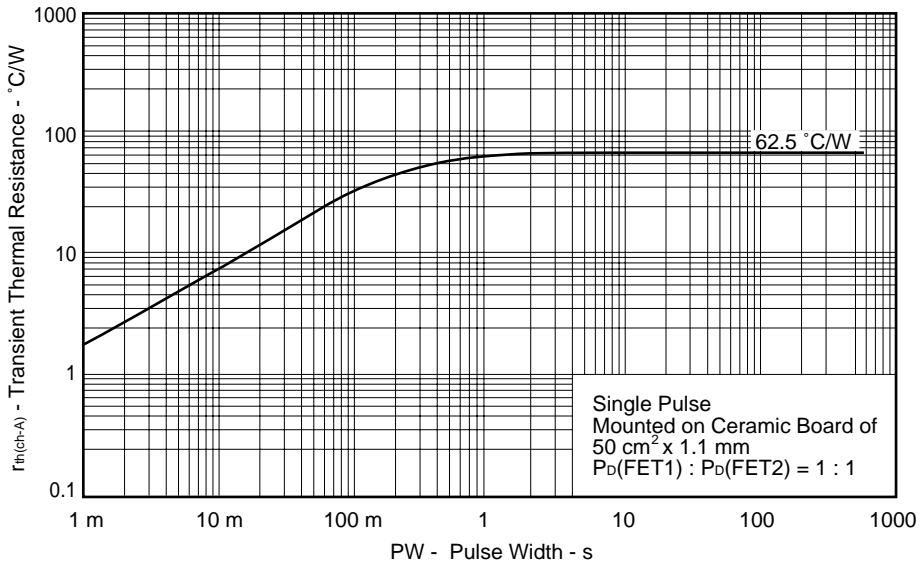
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



DYNAMIC INPUT CHARACTERISTICS



★ TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



[MEMO]

[MEMO]

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